TOSHIBA MOS INTEGRATED CIRCUIT

TC538000 AP / AF

SILICON GATE CMOS

8 MBIT (1 M WORD BY 8 BITS) CMOS MASK ROM

DESCRIPTION

The TC538000AP/AF is a 8,388,608-bit Read Only Memory organized as 1,048,576 words by 8 bits.

The TC538000AP/AF is fabricated using Toshiba's advanced CMOS technology which provides the high speed and low power features, an access time of 150 ns, an operation current of 40 mA at 6.7 MHz and a standby current of 100 μA.

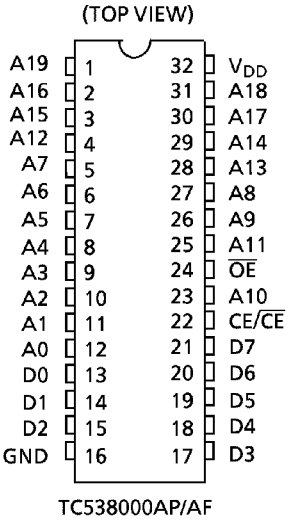
The TC538000AP/AF has one programmable Chip Enable input $\overline{CE}$/CE for device selection.

The TC538000AP/AF is packaged in a standard 600 mil 32-pin DIP/525 mil 32-pin SOP

FEATURES

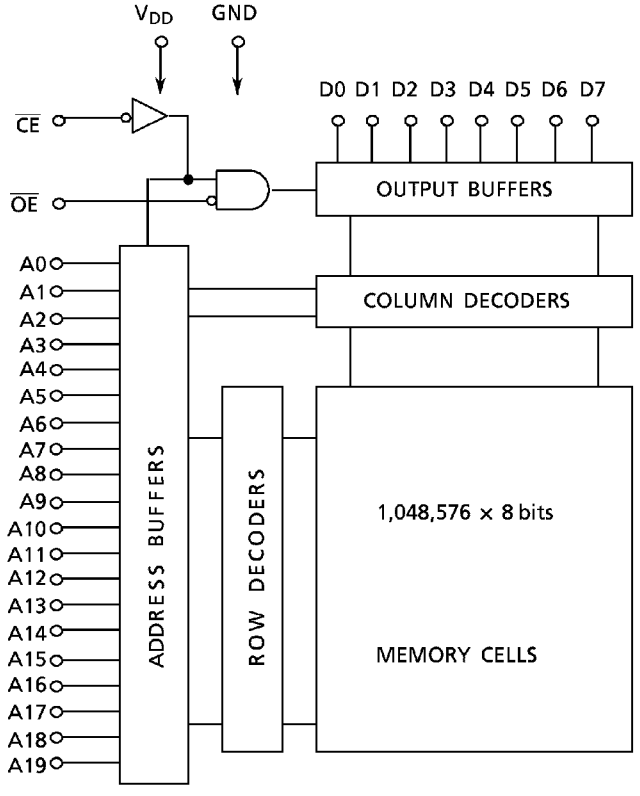
- Single 5 V Power Supply
- Access Time: 150 ns (max) V_{DD} = 5 V ± 10%
- Power Dissipation
  - Operating Current: 40 mA (max)
  - Standby Current : 100 μA (max)
- All Inputs and Outputs: TTL Compatible
- Three State Outputs
- Fully Static Operation
- Programmable Chip Enable
- TC538000AP: DIP32−P−600
  TC538000AF: SOP32−P−525

PIN ASSIGNMENT



TC538000AP/AF

BLOCK DIAGRAM



PIN NAMES

A0 to A19	Address Inputs
D0 to D7	Data Outputs
$\overline{OE}$	Output Enable Input
CE/$\overline{CE}$	Chip Enable Input
V_{DD}	Power Supply
GND	Ground

ABSOLUTE MAXIMUM RATINGS

SYMBOL	RATING	VALUE	UNIT
V_{DD}	Power Supply Voltage	− 0.5 to 7.0	V
V_{IN}	Input Voltage	− 0.5 to V_{DD}	V
V_{OUT}	Output Voltage	0 to V_{DD}	V
P_D	Power Dissipation	1.0/0.6*	W
T_{STG}	Storage Temperature	− 55 to 150	°C
T_{OPR}	Operating Temperature	0 to 70	°C
T_{SOLDER}	Soldering Temperature (10 s)	260	°C

Note: * SOP

DC RECOMMENDED OPERATING CONDITIONS (Ta = 0° to 70°C)

SYMBOL	PARAMETER	MIN	MAX	UNIT
V_{DD}	Power Supply Voltage	4.5	5.5	V
V_{IH}	Input High Voltage	2.2	V_{DD} + 0.3	V
V_{IL}	Input Low Voltage	− 0.3	0.8	V

DC CHARACTERISTICS (V_{DD} = 5 V ± 10%, Ta = 0° to 70°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{IL}	Input Leakage Current	V_{IN} = 0 to V_{DD}	−	± 5.0	μA
I_{LO}	Output Leakage Current	$\overline{CE}$ = V_{IH}, V_{OUT} = 0 to V_{DD}	−	± 5.0	μA
I_{OH}	Output High Current	V_{OH} = 2.4 V	− 1.0	−	mA
I_{OL}	Output Low Current	V_{OL} = 0.4 V	2.0	−	mA
I_{DDS1}	Standby Current	$\overline{CE}$ = V_{IH}	−	2	mA
I_{DDS2}		$\overline{CE}$ = V_{DD} and V_{IN} = 0 V (V_{DD})	−	100	μA
I_{DDO1}	Operating Current	V_{IN} = V_{IH}/V_{IL}, t_{cycle} = 150 ns	−	50	mA
I_{DDO2}		V_{IN} = V_{DD}/0 V, t_{cycle} = 150 ns	−	40	mA

CAPACITANCE

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
C_{IN}	Input Capacitance	f = 1 MHz, Ta = 25°C	−	10	pF
C_{OUT}	Output Capacitance	f = 1 MHz, Ta = 25°C	−	10	pF

Note: This parameter is periodically sampled and is not tested for every component.

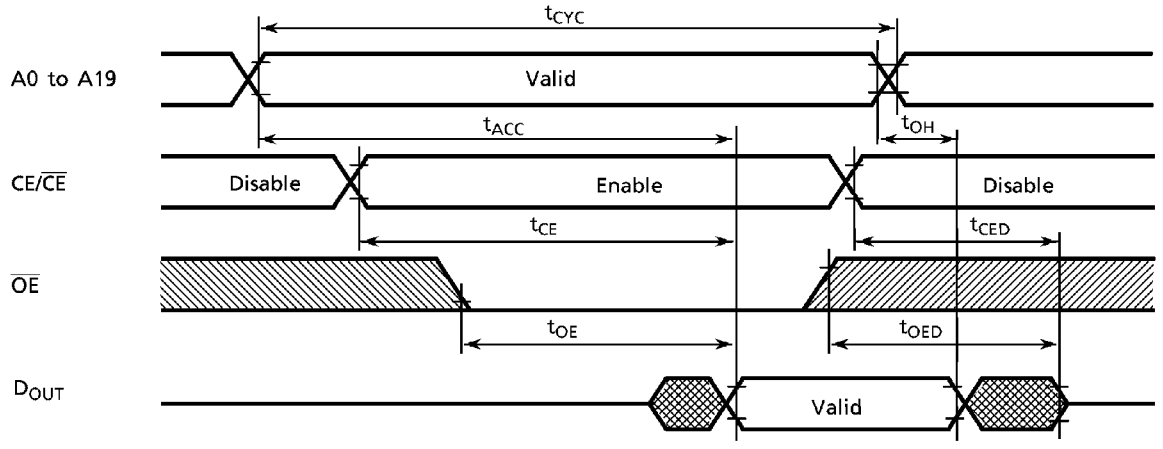
AC CHARACTERISTICS AND OPERATING CONDITIONS

SYMBOL	PARAMETER	MIN	MAX	UNIT
t_{ACC}	Access Time	–	150	ns
t_{CE}	Chip Enable Access Time	–	150	ns
t_{OE}	Output Enable Access Time	–	70	ns
t_{CED}	Output Disable Time from $\overline{CE}$	0	60	ns
t_{OED}	Output Disable Time from $\overline{OE}$	0	60	ns
t_{OH}	Output Hold Time	5	–	ns
t_{CYC}	Cycle Time	150	–	ns

AC TEST CONDITIONS

Output Load : 100 pF + 1 TTL
Input Levels : 0.6 V, 2.4 V
Timing Measurement Reference Levels Input : 0.8 V, 2.2 V
Output: 0.8 V, 2.0 V
Input Rise and Fall Time : 5 ns

TIMING DIAGRAMS



OPERATION MODES

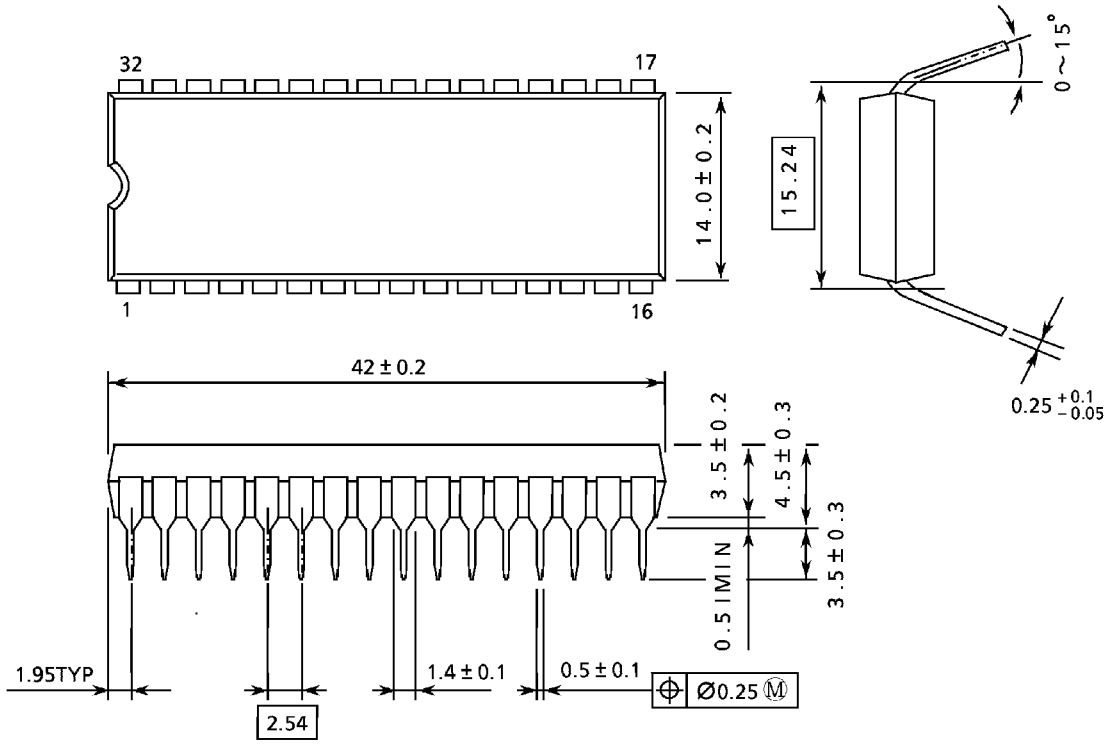
MODE	$\overline{CE}$ (CE)	$\overline{OE}$	A0 to A19	OUTPUTS	POWER
Read	L (H)	L	Valid	Data Out	Operating
Standby	H (L)	*	*	High-Z	Standby
Output Deselect	L (H)	H	*	High-Z	Operating

H: V_{IH} L: V_{IL} *: V_{IH} or V_{IL}

PACKAGE DIMENSIONS

Plastic DIP (DIP32−P−600)

UNITS: mm



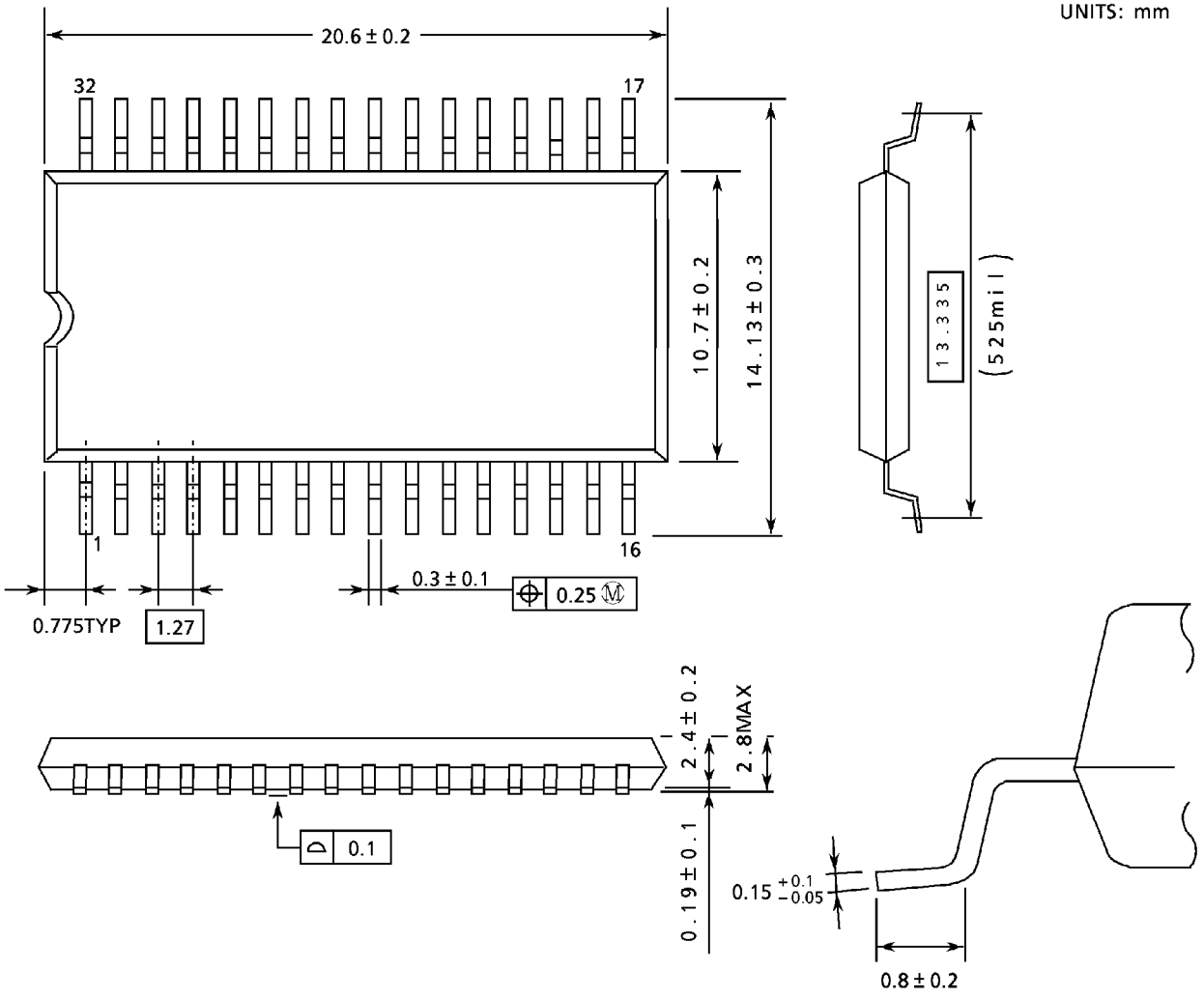
Weight: 4.5 g (typ)

Note: Package width and length do not include mold protrusion. The permissible mold protrusion is 0.15 mm.

PACKAGE DIMENSIONS

Plastic FP (SOP32−P−525)

UNITS: mm



Weight: 1.1 g (typ)

Note: Package width and length do not include mold protrusion. The permissible mold protrusion is 0.15 mm.